



MMST2222A

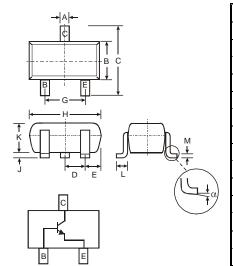
NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMST2907A)
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: K3P See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.006 grams (approximate)



	SOT-323										
Dim	Min	Max									
Α	0.25	0.40									
В	1.15	1.35									
С	2.00	2.20									
D	0.65 N	ominal									
E	0.30	0.40									
G	1.20	1.40									
Н	1.80	2.20									
7	0.0	0.10									
K	0.90	1.00									
L	0.25	0.40									
М	0.10	0.18									
α	0°	8°									
All Din	All Dimensions in mm										

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current – Continuous (Note 1)	Ic	600	mA
Power Dissipation (Note 1)	Pd	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes:

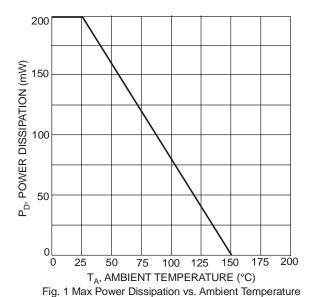
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

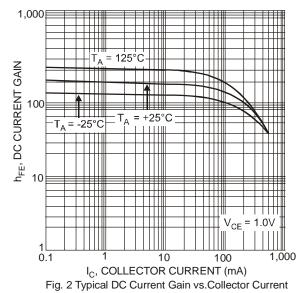


Electrical Characteristics @T_A = 25°C unless otherwise specified

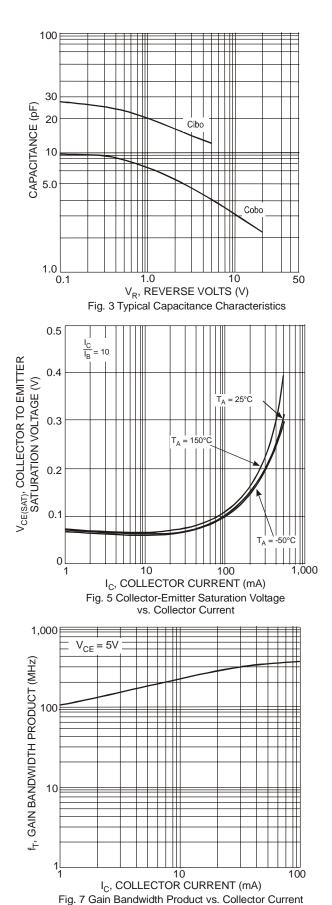
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	75	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	_	V	$I_E = 10\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	10	nA μA	$V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0, T_{A} = 150^{\circ}C$
Collector Cutoff Current	I _{CEX}	_	10	nA	$V_{CE} = 60V, V_{EB(OFF)} = 3.0V$
Emitter Cutoff Current	I _{EBO}	_	10	nA	V _{EB} = 3.0V, I _C = 0
Base Cutoff Current	I _{BL}	_	20	nA	$V_{CE} = 60V, V_{EB(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 5)				•	. ==(=::,
DC Current Gain	h _{FE}	35 50 75 100 40 50 35		_	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 10 V \\ I_C &= 1.0 m A, \ V_{CE} = 10 V \\ I_C &= 10 m A, \ V_{CE} = 10 V \\ I_C &= 150 m A, \ V_{CE} = 10 V \\ I_C &= 500 m A, \ V_{CE} = 10 V \\ I_C &= 10 m A, \ V_{CE} = 10 V, \ T_A = -55^{\circ} C \\ I_C &= 150 m A, \ V_{CE} = 1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.3 1.0	V	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.6	1.2 2.0	V	$I_{C} = 150 \text{mA}, I_{B} = 15 \text{mA}$ $I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}		8	pF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	Cibo		25	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Current Gain-Bandwith Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_{C} = 20mA,$ f = 1.0MHz
Noise Figure	NF	_	4.0	dB	V_{CE} = 10V, I_{C} = 100μA, R_{S} = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d		10	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	t _r	_	25	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = 15mA$
Storage Time	ts		225	ns	V _{CC} = 30V, I _C = 150mA,
Fall Time	t _f	_	60	ns	$I_{B1} = I_{B2} = 15mA$

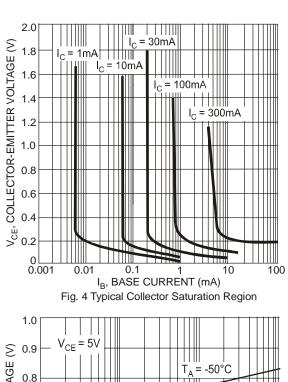
^{5.} Short duration pulse test used to minimize self-heating effect.

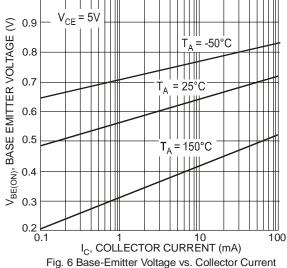












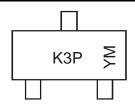


Ordering Information (Notes 4 & 6)

Device	Packaging	Shipping
MMST2222A-7-F	SOT-323	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K3P = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	J	V	W	Χ	Υ	Z

Mor	ıth	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Cod	de	1	2	3	4	5	6	7	8	9	0	N	D

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